

Simulation of electric field profile in Si irradiated detectors with a consideration of carrier generation parameters

Thursday, November 15, 2012 12:30 PM (20 minutes)

Impact of the parameters which define bulk generation current of Si irradiated detectors on the detector characteristics is analyzed. The electric field profile and space charge/free carrier concentrations are simulated regarding generation current and carrier generation lifetime.

Primary author: Dr VERBITSKAYA, Elena (Ioffe Physical-Technical Institute of Russian Academy of Sciences)

Co-author: Dr EREMIN, Vladimir (Ioffe Physical-Technical Institute of Russian Academy of Sciences)

Presenter: Dr VERBITSKAYA, Elena (Ioffe Physical-Technical Institute of Russian Academy of Sciences)

Session Classification: Detector Characterization and Simulations

Track Classification: Simulations